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# FQS4903

## N-Channel QFET® MOSFET

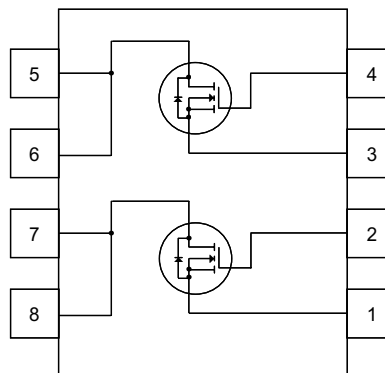
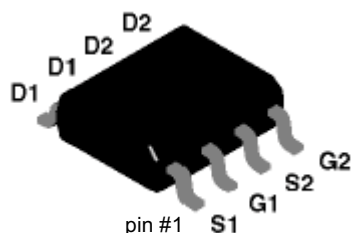
500 V, 0.37 A, 6.2 Ω

### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

### Features

- 0.37 A, 500 V,  $R_{DS(on)}=6.2 \Omega(\text{Max.})@V_{GS}=10 \text{ V}, I_D=0.185 \text{ A}$
- Low Gate Charge (Typ. 6.3 nC)
- Low  $C_{rss}$  (Typ. 4.5 pF)
- 100% Avalanche Tested



### Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQS4903	Unit
$V_{DSS}$	Drain-Source Voltage	500	V
$I_D$	Drain Current - Continuous ( $T_A = 25^\circ\text{C}$ )	0.37	A
		0.234	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	1.48	A
$V_{GSS}$	Gate-Source Voltage	$\pm 25$	V
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
$P_D$	Power Dissipation ( $T_A = 25^\circ\text{C}$ )	2.0	W
		1.3	W
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C/W}$

**Electrical Characteristics** $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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**Off Characteristics**

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	500	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.49	--	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	$\mu\text{A}$
		$V_{DS} = 400\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 25\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -25\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

**On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 0.185\text{ A}$	--	4.7	6.2	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 35\text{ V}, I_D = 0.185\text{ A}$ (Note 3)	--	0.13	--	S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	155	200	pF
$C_{oss}$	Output Capacitance		--	25	35	pF
$C_{rss}$	Reverse Transfer Capacitance		--	4.5	6.0	pF

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250\text{ V}, I_D = 0.37\text{ A},$ $R_G = 25\ \Omega$	--	5.5	20	ns
$t_r$	Turn-On Rise Time		--	20	50	ns
$t_{d(off)}$	Turn-Off Delay Time		--	20	50	ns
$t_f$	Turn-Off Fall Time		(Note 3,4)	--	45	100
$Q_g$	Total Gate Charge	$V_{DS} = 400\text{ V}, I_D = 0.37\text{ A},$ $V_{GS} = 10\text{ V}$	--	6.3	8.2	nC
$Q_{gs}$	Gate-Source Charge		--	0.56	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 3,4)	--	3.63	--

**Drain-Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	0.37	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	1.48	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 0.37\text{ A}$	--	--	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 0.37\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	100	--	ns
$Q_{rr}$	Reverse Recovery Charge		(Note 3)	--	0.175	--

**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
3.  $I_{SD} \leq 0.37\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\ \mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

## Typical Characteristics

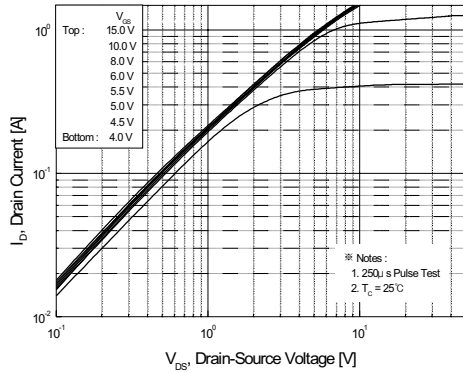


Figure 1. On-Region Characteristics

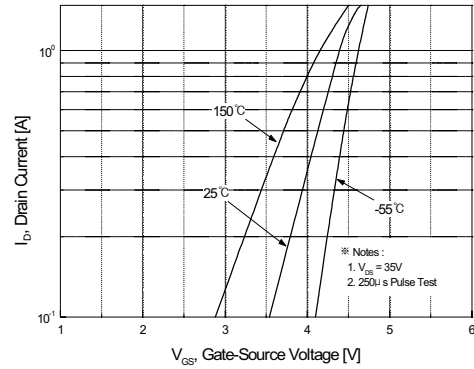


Figure 2. Transfer Characteristics

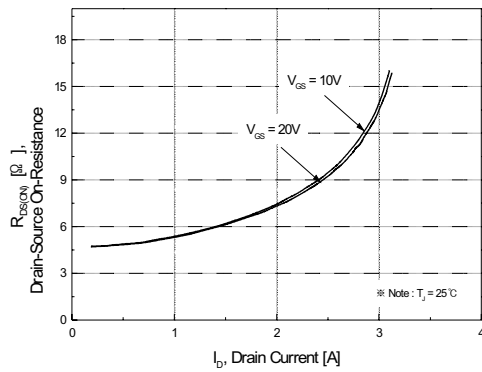


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

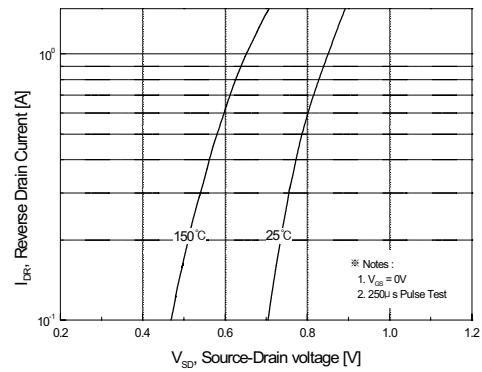


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

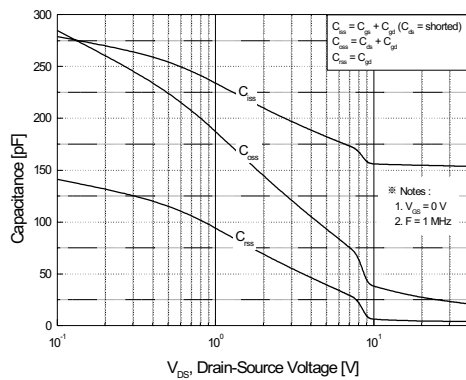


Figure 5. Capacitance Characteristics

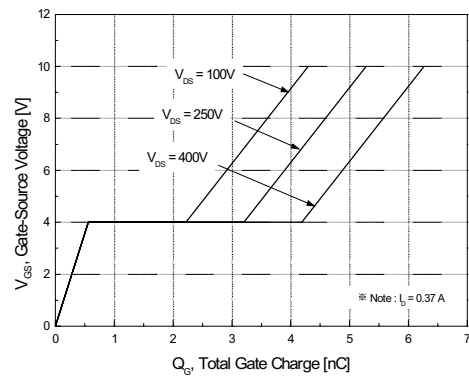
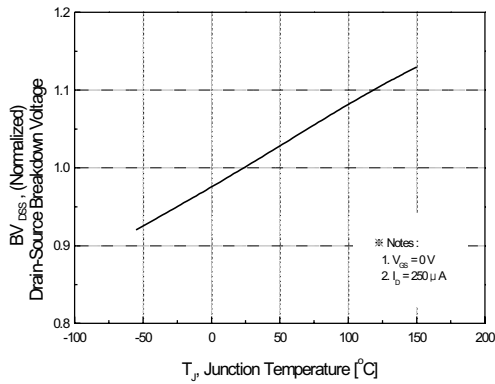
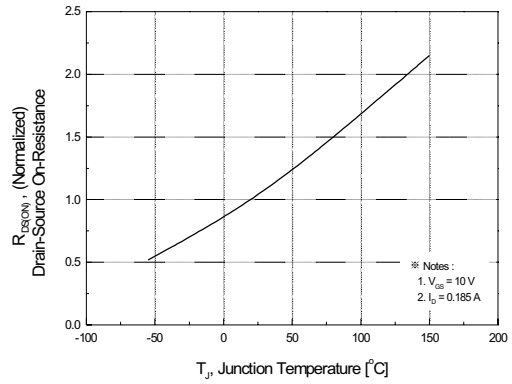


Figure 6. Gate Charge Characteristics

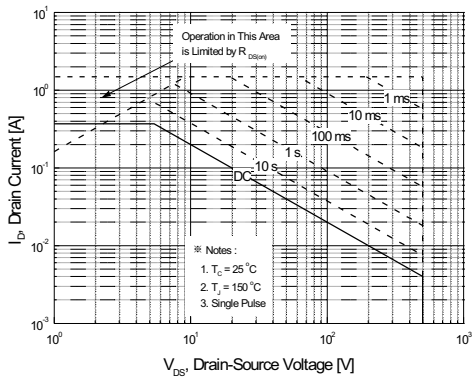
**Typical Characteristics** (Continued)



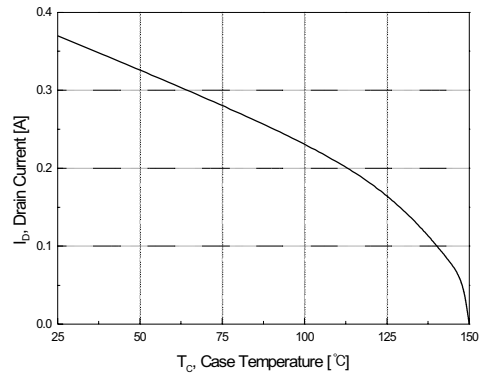
**Figure 7. Breakdown Voltage Variation vs. Temperature**



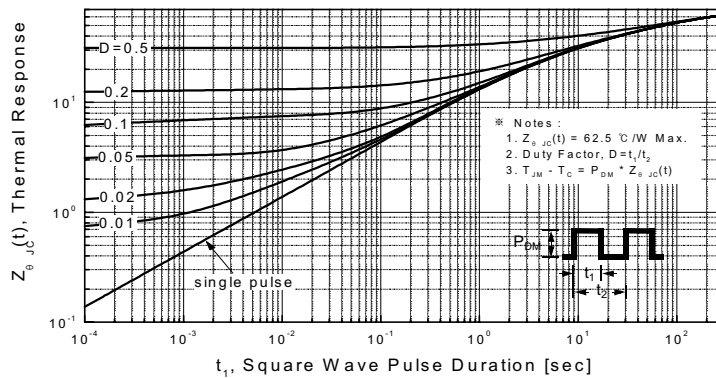
**Figure 8. On-Resistance Variation vs. Temperature**



**Figure 9. Maximum Safe Operating Area**

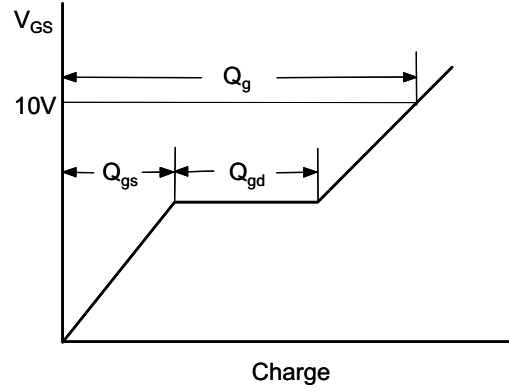
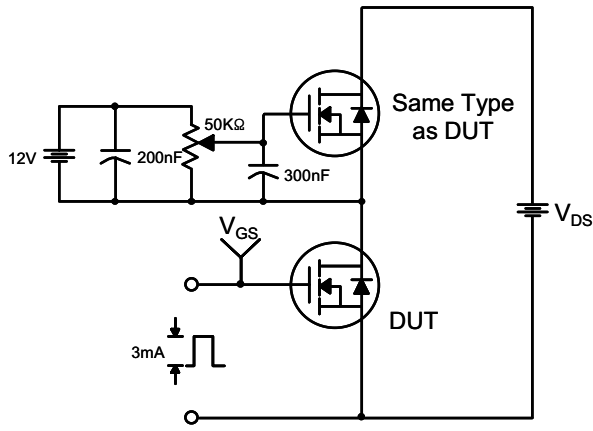


**Figure 10. Maximum Drain Current vs. Case Temperature**

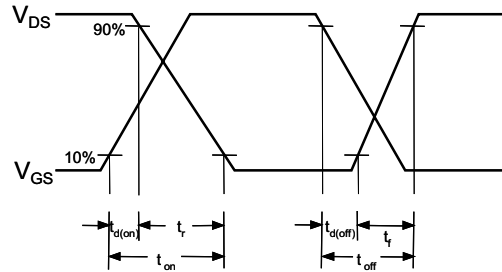
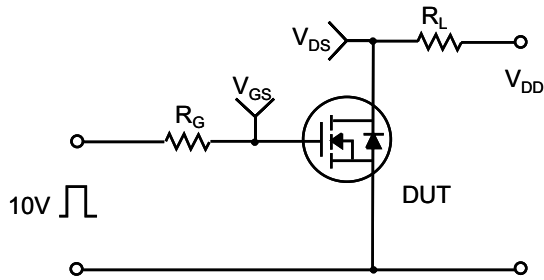


**Figure 11. Transient Thermal Response Curve**

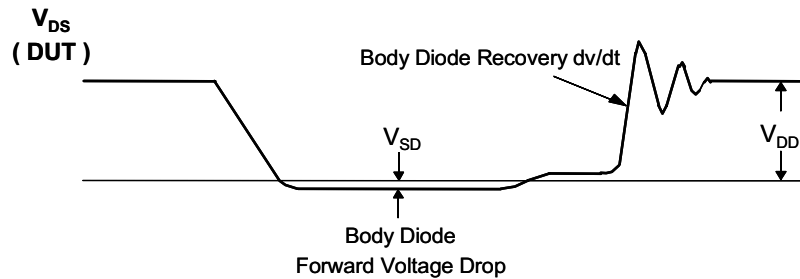
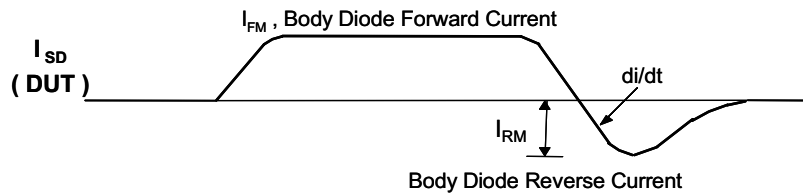
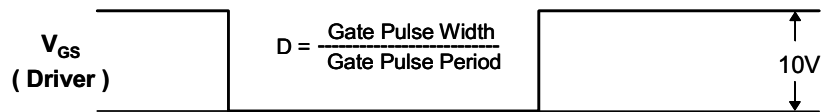
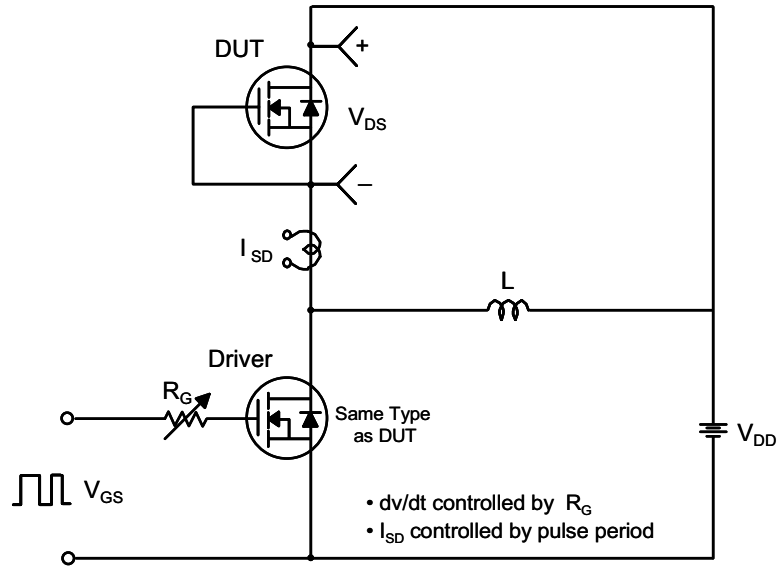
**Gate Charge Test Circuit & Waveform**



**Resistive Switching Test Circuit & Waveforms**

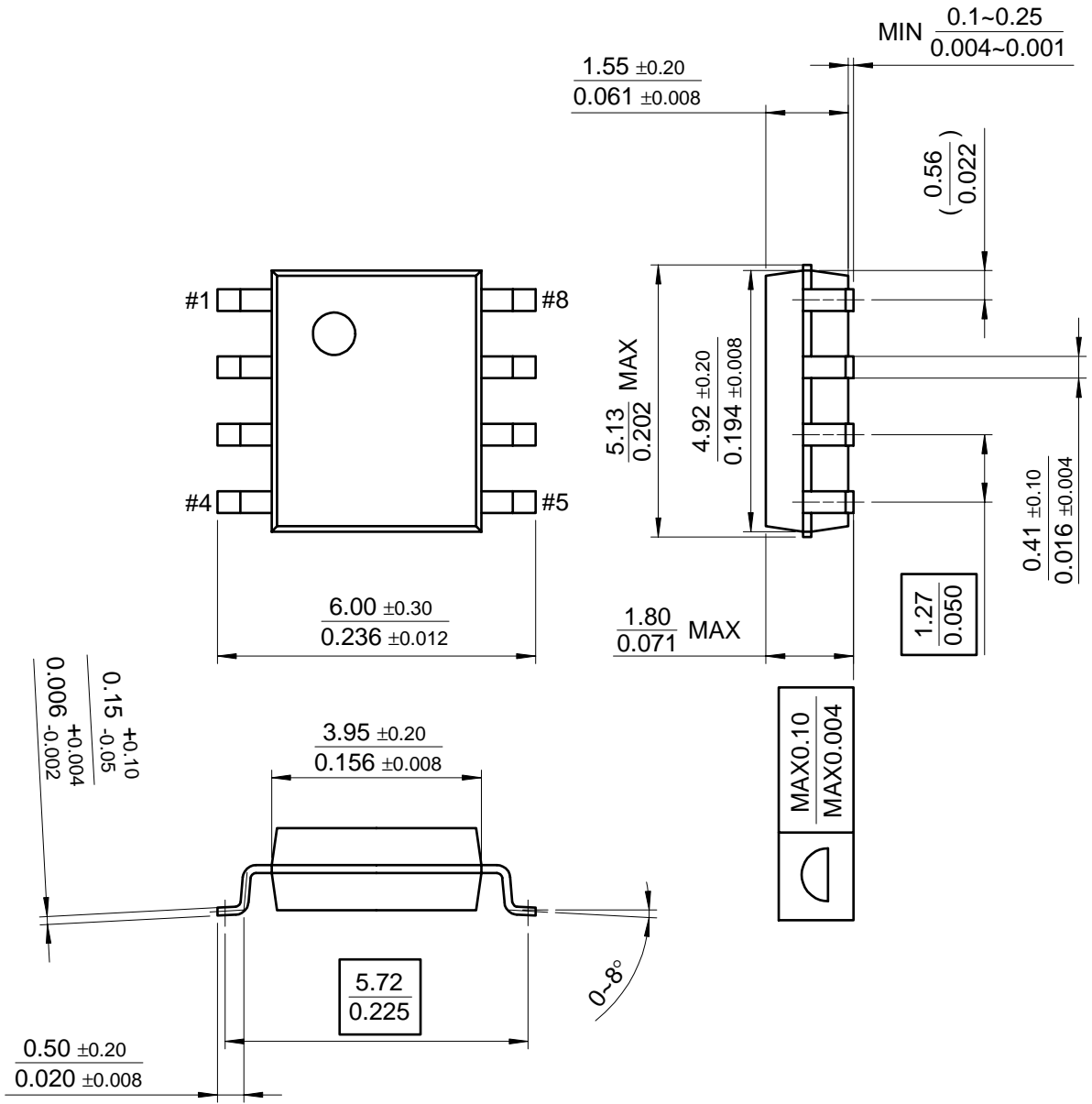


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

8SOP







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| CorePOWER™               | Green FPS™ e-Series™                            | TINYOPTO™        |
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